

Silicon PNP Power Transistors

2SB1085A

DESCRIPTION

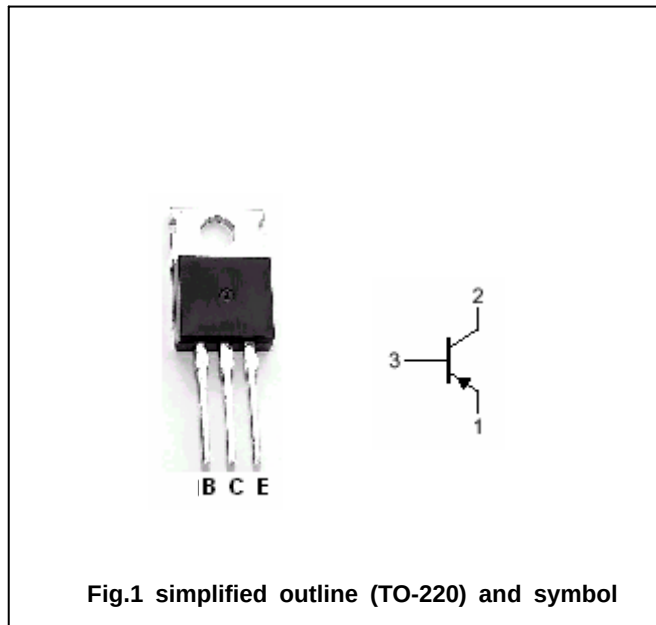
- With TO-220 package
- Complement to type 2SD1562A
- Low collector saturation voltage

APPLICATIONS

- Designed for use in low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-160	V
V_{CEO}	Collector-emitter voltage	Open base	-160	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-1.5	A
I_{CM}	Collector current-peak		-3.0	A
P_C	Collector power dissipation	$T_C=25^{\circ}\text{C}$	20	W
T_j	Junction temperature		150	$^{\circ}\text{C}$
T_{stg}	Storage temperature		-55~150	$^{\circ}\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-1mA, I_B=0$	-160			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=-50\mu A, I_E=0$	-160			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=-50\mu A, I_C=0$	-5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-1A; I_B=-0.1A$			-2.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=-1A; I_B=-0.1A$			-1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=-120V; I_E=0$			-1.0	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-4V; I_C=0$			-1.0	μA
h_{FE}	DC current gain	$I_C=-0.1A; V_{CE}=-5V$	60		200	
C_{OB}	Output capacitance	$I_E=0; V_{CB}=-10V, f=1MHz$		30		pF
f_T	Transition frequency	$I_C=-0.1A; V_{CE}=-5V$		50		MHz

◆ h_{FE} classifications

D	E
60-120	100-200

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PACKAGE OUTLINE

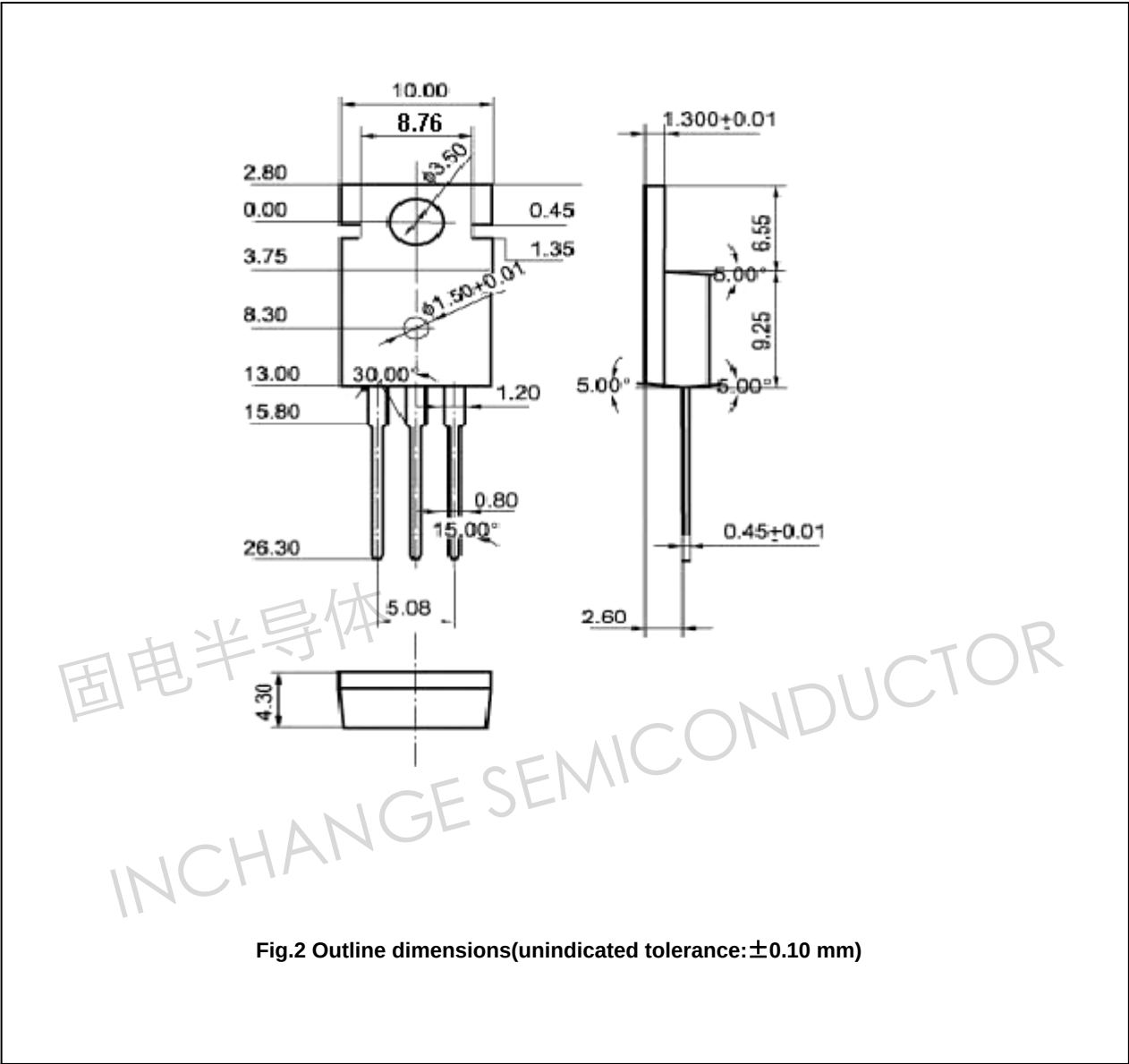


Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)